Unit in mm

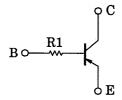
TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT Process)

RN2112F,RN2113F

Switching, Inverter Circuit, Interface Circuit And Driver Circuit Applications

- With built-in bias resistors
- Simplify circuit design
- Reduce a quantity of parts and manufacturing process
- Complementary to RN1112F, RN1113F

Equivalent Circuit



Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-50	V
Collector-emitter voltage	V _{CEO}	-50	V
Emitter-base voltage	V _{EBO}	-5	V
Collector current	Ic	-100	mA
Collector power dissipation	PC	100	mW
Junction temperature	Tj	150	°C
Storage temperature range	T _{stg}	-55~150	°C

1. BASE
2. EMITTER
3. COLLECTOR

2-2HA1A

Weight: 2.3 mg

JEDEC EIAJ TOSHIBA

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In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent TOSHIBA products specifications. Also, please keep in mind the precautions and conditions set forth in the "Handling Guide for Semiconductor Devices," or "TOSHIBA Semiconductor Reliability Handbook" etc..

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• The information contained herein is subject to change without notice.

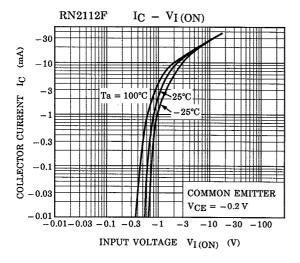
[•] TOSHIBA is continually working to improve the quality and reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to comply with the standards of safety in making a safe design for the entire system, and to avoid situations in which a malfunction or failure of such TOSHIBA products could cause loss of human life, bodily injury or damage to property.

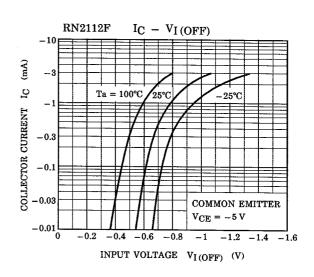
[•] The TOSHIBA products listed in this document are intended for usage in general electronics applications (computer, personal equipment, office equipment, measuring equipment, industrial robotics, domestic appliances, etc.). These TOSHIBA products are neither intended nor warranted for usage in equipment that requires extraordinarily high quality and/or reliability or a malfunction or failure of which may cause loss of human life or bodily injury ("Unintended Usage"). Unintended Usage include atomic energy control instruments, airplane or spaceship instruments, transportation instruments, traffic signal instruments, combustion control instruments, medical instruments, all types of safety devices, etc.. Unintended Usage of TOSHIBA products listed in this document shall be made at the customer's own risk.

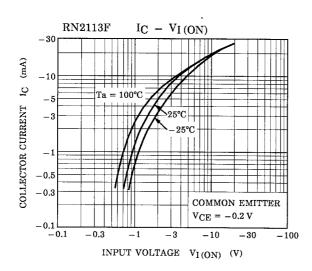


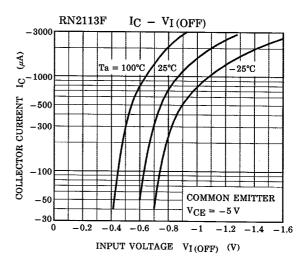
Electrical Characteristics (Ta = 25°C)

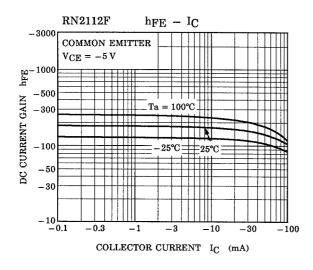
Characteristic		Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current		I _{CBO}	_	$V_{CB} = -50V$, $I_E = 0$	_	_	-100	nA
Emitter cut-off current		I _{EBO}	_	$V_{EB} = -5V, I_C = 0$	_	_	-100	nA
DC current gain		h _{FE}	_	$V_{CE} = -5V, I_{C} = -1mA$	120	_	400	_
Collector-emitter saturation voltage		V _{CE} (sat)	_	$I_C = -5mA$, $I_B = -0.25mA$	_	-0.1	-0.3	V
Transition frequency		f _T	_	V _{CE} = −10V, I _C = −5mA	_	200	_	MHz
Collector output capacitance		C _{ob}	_	V _{CB} = −10V, I _E = 0, f = 1MHz	_	3	6	pF
Input resistor	RN2112F	- R1	_	_	15.4	22	28.6	kΩ
	RN2113F				32.9	47	61.1	

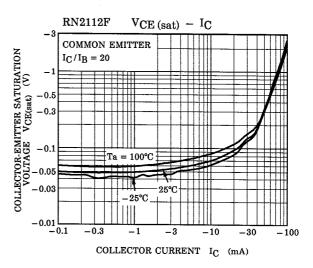


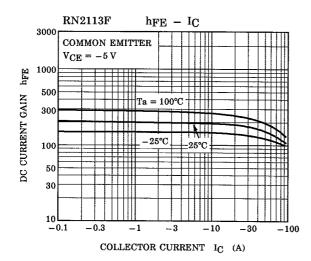


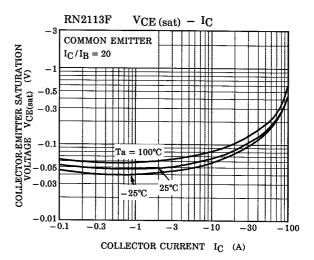












Type Name	Marking	
RN2112F	Type Name Y N	
RN2113F	Type Name Y P	